PROCESS CPD06

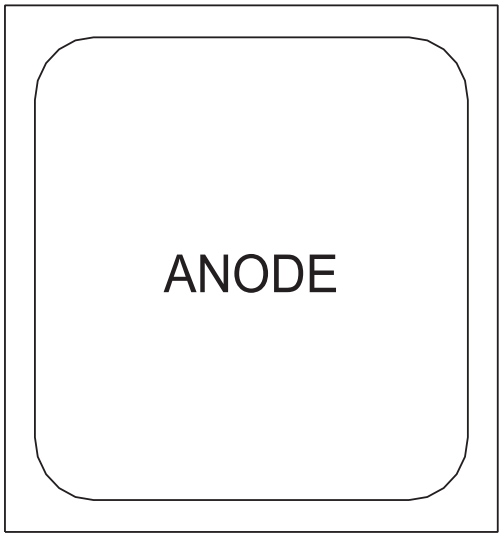
General Purpose Rectifier

3 Amp Glass Passivated Rectifier Chip

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	89 x 89 MILS
Die Thickness	10.2 MILS
Anode Bonding Pad Area	66 x 66 MILS
Top Side Metalization	Ni/Au - 5,000Å/2,000Å
Back Side Metalization	Ni/Au - 5,000Å/2,000Å

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 4 INCH WAFER

1,490

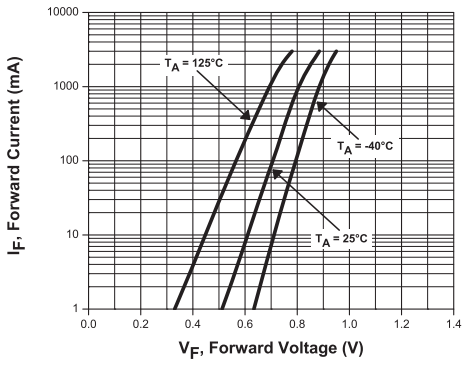
PRINCIPAL DEVICE TYPES

1N5400 thru 1N5408
1N5550 thru 1N5554
1N5624 thru 1N5627
CMR3-02 Series

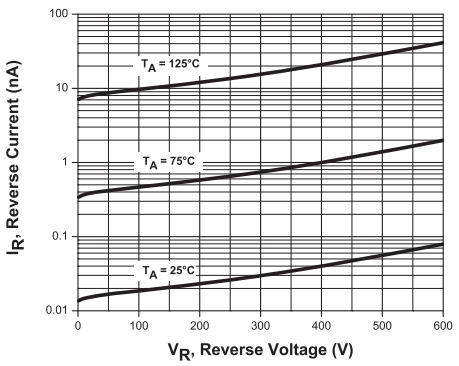
PROCESS CPD06

Typical Electrical Characteristics

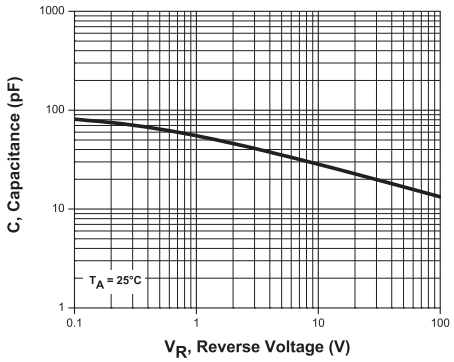
Forward Voltage



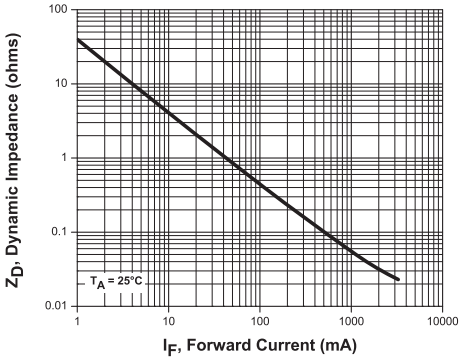
Leakage Current



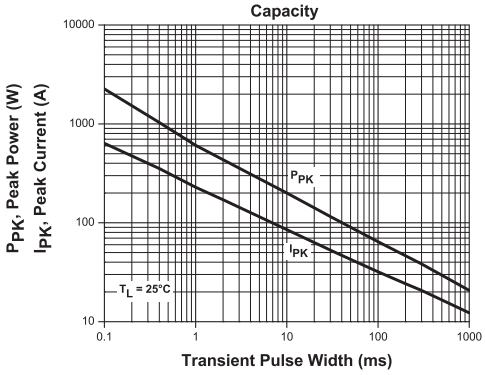
Capacitance



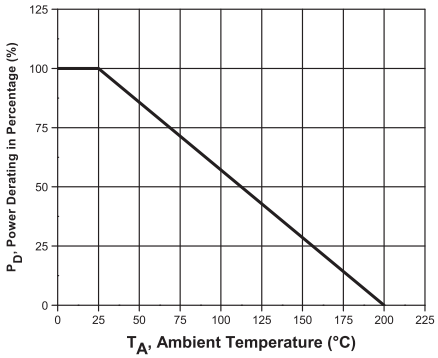
Forward Dynamic Impedance



Transient Peak Power and Peak Current Capacity



Normalized Power Derating



R4 (22-March 2010)